



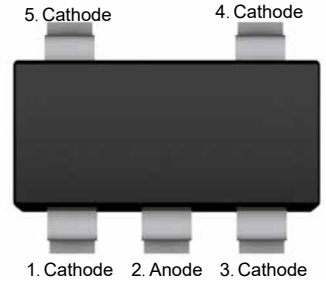
# MMBP187SE

## Silicon Epitaxial Planar Switching Diode

**Features:**

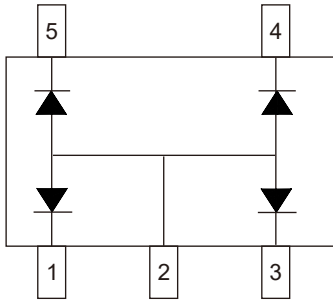
- High Speed switching

**Package:** GCH187-5



**Marking Code:** P187

**Electrical Symbol:**



**Electrical Characteristics (at  $T_J = 25^\circ\text{C}$ ):**

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	$V_{RRM}$	80	V
Reverse Voltage	$V_R$	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	1 4	A
		at $t = 1\text{s}$ at $t = 1\mu\text{s}$	
Maximum Power Dissipation	$P_D$	350	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics (at  $T_J = 25^\circ\text{C}$ ):**

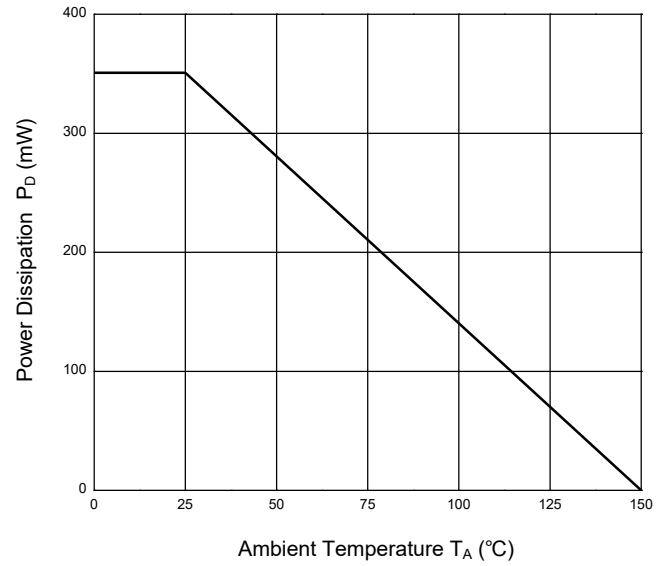
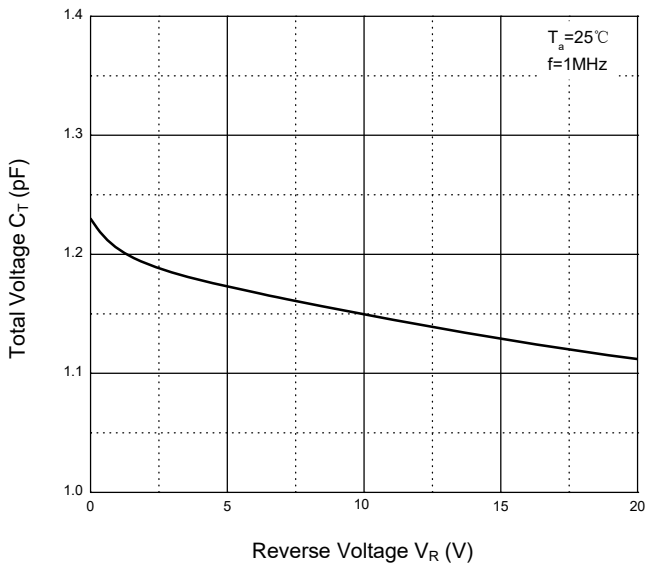
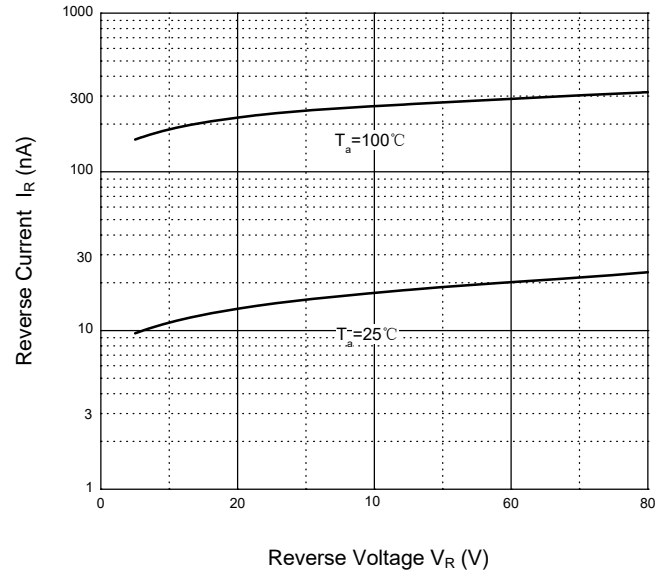
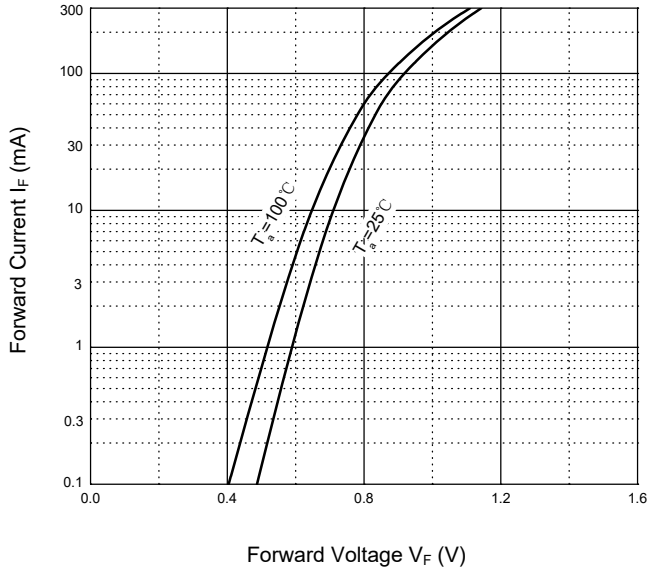
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage	$V_F$	--	0.7	V
at $I_F = 5\text{ mA}$		--	0.85	
at $I_F = 10\text{ mA}$				
Reverse Breakdown Voltage at $I_R = 100\ \mu\text{A}$	$V_{(BR)R}$	80	--	
Reverse Current at $V_R = 80\text{ V}$	$I_R$	--	1	$\mu\text{A}$
Typical Junction Capacitance	$C_j$	--	3	pF
at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$				
Maximum Reverse Recovery Time	$T_{rr}$	--	4	nS
at $I_F = I_R = 10\text{ mA}$ , $I_{rr} = 0.1 \times I_R$				



# MMBP187SE<sup>†</sup>

## Silicon Epitaxial Planar Switching Diode

### Typical Characteristic Curves





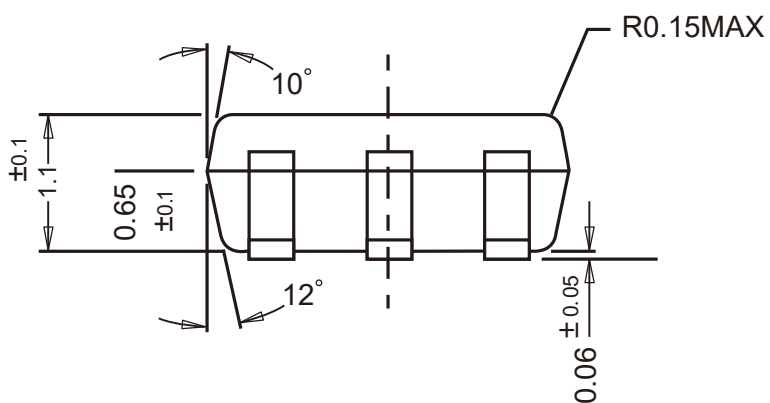
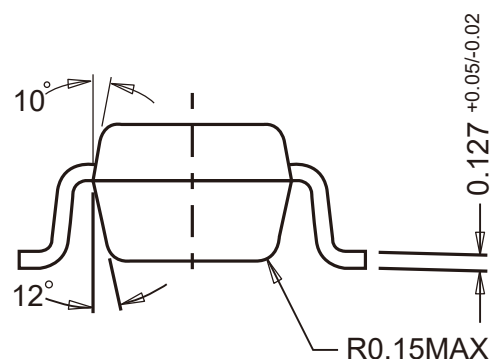
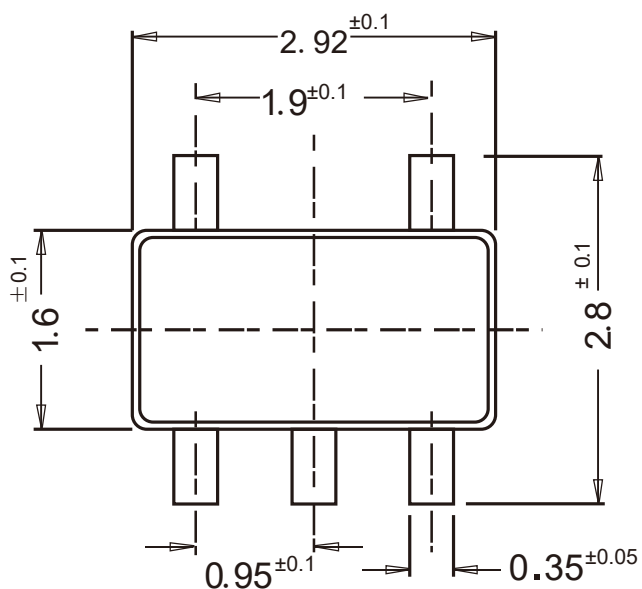
# MMBP187SE<sup>®</sup>

## Silicon Epitaxial Planar Switching Diode

### Package Outline

SOT-23-5

Dimensions in mm



### Ordering Information

Device	Package	Shipping
MMBP187SE	SOT-23-5	3,000PCS/Reel&7inches